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**Magnetotransport behavior in  $(\text{LaNiO}_3)_n/(\text{LaMnO}_3)_2$  superlattices** JASON HOFFMAN, Materials Science Division, Argonne National Laboratory, ANAND BHATTACHARYA, Materials Science Division and Center for Nanoscale Materials, Argonne National Laboratory — Recent advances in the deposition of epitaxial complex oxides have enabled the fabrication of a wide range of materials structures with atomically abrupt interfaces, that are characterized by novel electronic and magnetic ground states. In particular, superlattices that combine the paramagnetic metal,  $\text{LaNiO}_3$ , with various band insulators, such as  $\text{SrTiO}_3$  and  $\text{LaAlO}_3$ , have attracted considerable theoretical and experimental interest. In this work,  $(\text{LaNiO}_3)_n/(\text{LaMnO}_3)_2$  ( $2 \leq n \leq 5$ ) superlattices that combine  $\text{LaNiO}_3$  with an antiferromagnetic insulator are prepared on (001)  $\text{SrTiO}_3$  substrates using ozone-assisted oxide molecular beam epitaxy. The total superlattice thickness is fixed at  $\sim 30$  nm. X-ray reflectivity and x-ray diffraction reveal single-crystalline growth with interfacial and surface roughnesses of  $\sim 0.2$  nm and  $\sim 0.5$  nm, respectively. Electrical transport measurements carried out on superlattices with  $n \leq 3$  show insulating behavior between 5 K and 300 K, while samples with  $n = 4, 5$  are metallic with resistivity minima at 90 K and 30 K, respectively, below which we observe negative magnetoresistance. We discuss the role of charge transfer between  $\text{LaNiO}_3$  and  $\text{LaMnO}_3$  in understanding these results.

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